



UTT30N06

Power MOSFET

**30A, 60V N-CHANNEL
POWER MOSFET**

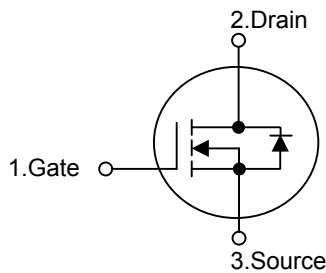
■ DESCRIPTION

The UTC **UTT30N06** is a low voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and excellent avalanche characteristics. This power MOSFET is usually used in automotive applications of power supplies, high efficient DC to DC converters and battery operated products.

■ FEATURES

- * $R_{DS(ON)} = 40m\Omega @ V_{GS} = 10V$
- * Ultra low gate charge (typical 20 nC)
- * Low reverse transfer Capacitance ($C_{RSS} =$ typical 80 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability

■ SYMBOL

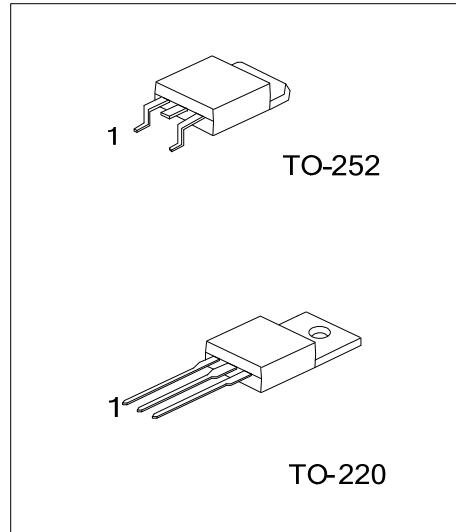


■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTT30N06L-TN3-R	UTT30N06G-TN3-R	TO-252	G	D	S	Tape Reel
UTT30N06L-TA3-T	UTT30N06G-TA3-T	TO-220	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UTT30N06L-TN3-R</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Lead Free</p>	<p>(1) R: Tape Reel, T: Tube</p> <p>(2) TN3: TO-252, TA3: TO-220</p> <p>(3) G: Halogen Free, L: Lead Free</p>
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■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	60	V	
Gate-Source Voltage		V_{GSS}	± 20	V	
Drain Current	Continuous	I_D	$T_C = 25^{\circ}\text{C}$	30	A
			$T_C = 100^{\circ}\text{C}$	21.3	A
	Pulsed (Note 1)		I_{DM}	120	A
Avalanche Energy	Single Pulsed (Note 2)		E_{AS}	300	mJ
	Repetitive (Note 1)		E_{AR}	8	mJ
Peak Diode Recovery dv/dt (Note 3)		dv/dt	7.5	V/ns	
Power Dissipation	TO-220	P_D	89	W	
	TO-252		44		
Junction Temperature		T_J	+150	$^{\circ}\text{C}$	
Operation Temperature		T_{OPR}	-55~+150	$^{\circ}\text{C}$	
Storage Temperature		T_{STG}	-55~+150	$^{\circ}\text{C}$	

Notes: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

1. Repeativity rating: pulse width limited by junction temperature
2. $L=0.66\text{mH}$, $I_{AS}=30\text{A}$, $V_{DD}=25\text{V}$, $R_G=20\Omega$, Starting $T_J=25^{\circ}\text{C}$
3. $I_{SD}\leq 50\text{A}$, $di/dt\leq 300\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J=25^{\circ}\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220	θ_{JA}	62	$^{\circ}\text{C}/\text{W}$
	TO-252		50	
Junction to Case	TO-220	θ_{JC}	1.4	$^{\circ}\text{C}/\text{W}$
	TO-252		2.85	

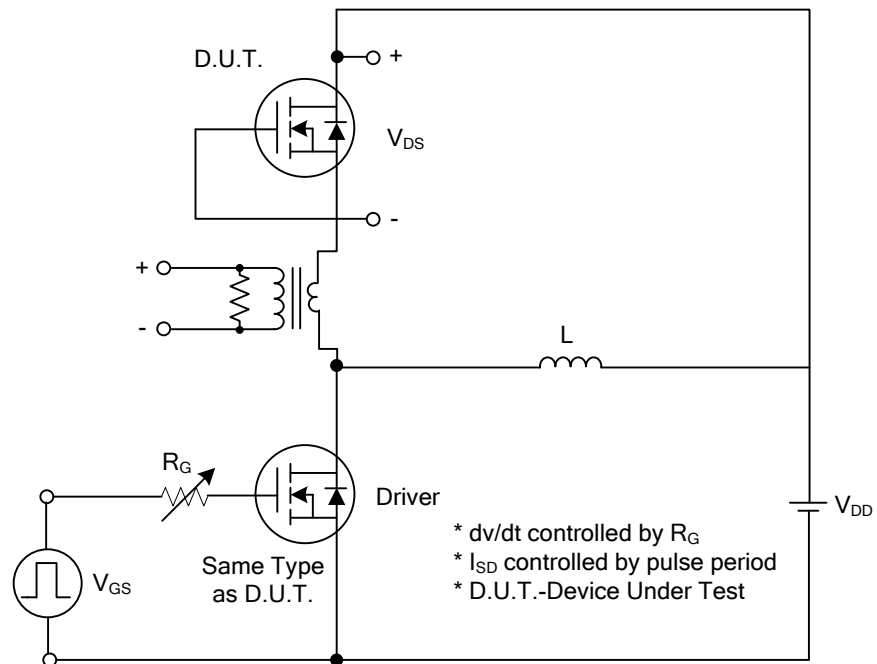
■ ELECTRICAL CHARACTERISTICS (T_c=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 250 μA	60			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS} V _{GS} = 20V, V _{DS} = 0 V			100	nA
	Reverse		V _{GS} = -20V, V _{DS} = 0 V			-100
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.06		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 15 A		32	40	mΩ
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1MHz		800		pF
Output Capacitance	C _{OSS}			300		pF
Reverse Transfer Capacitance	C _{RSS}			80		pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 30V, I _D = 15 A, V _{GS} = 10V (Note 1, 2)		12		ns
Turn-On Rise Time	t _R			79		ns
Turn-Off Delay Time	t _{D(OFF)}			50		ns
Turn-Off Fall Time	t _F			52		ns
Total Gate Charge	Q _G	V _{DS} = 60V, V _{GS} = 10 V, I _D = 24A (Note 1, 2)		20	30	nC
Gate-Source Charge	Q _{GS}			6		nC
Gate-Drain Charge	Q _{GD}			9		nC
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 30A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I _S				30	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				120	A
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, I _S = 30A,		40		ns
Reverse Recovery Charge	Q _{RR}	dI _F / dt = 100 A/μs (Note 1)		70		μC

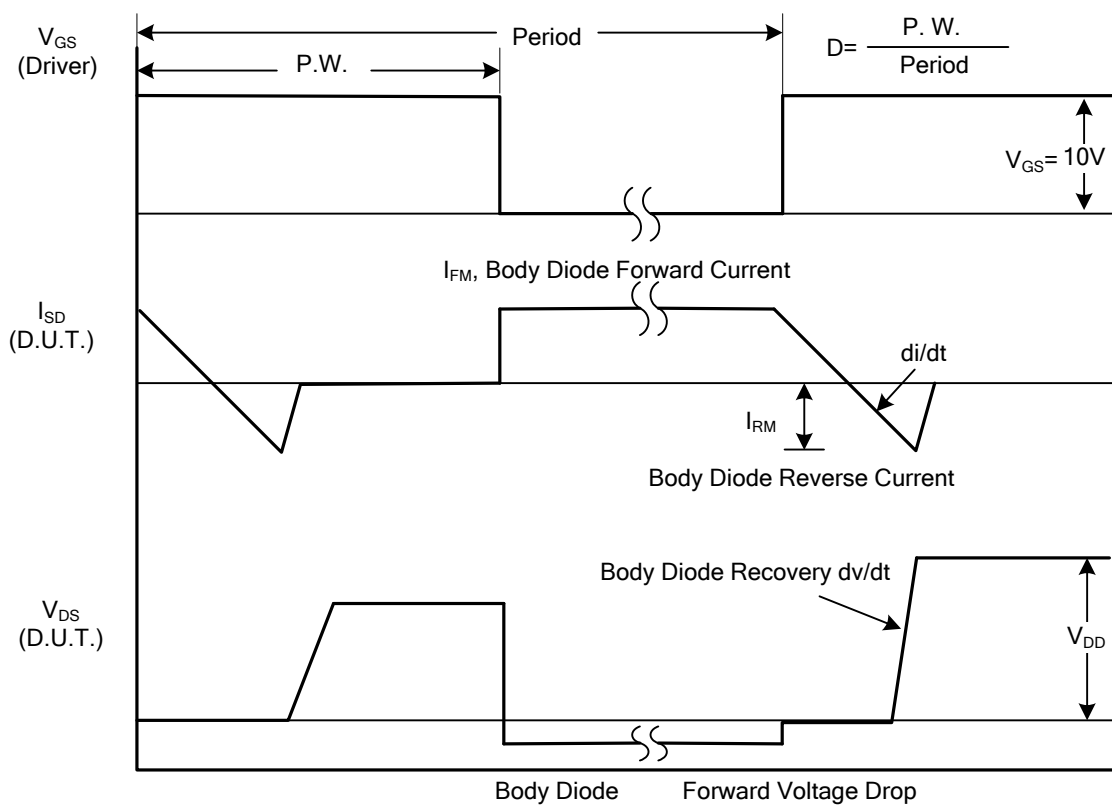
Notes: 1. Pulse Test : Pulse width ≤300μs, Duty cycle ≤ 2%

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

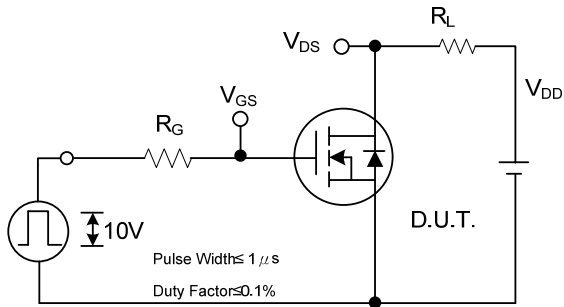


Peak Diode Recovery dv/dt Test Circuit

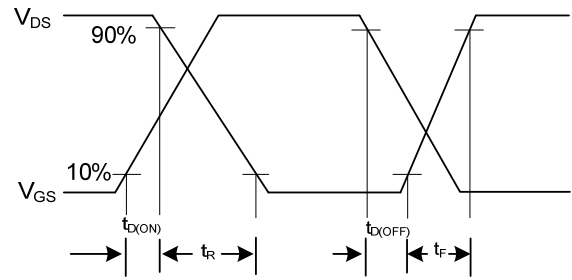


Peak Diode Recovery dv/dt Waveforms

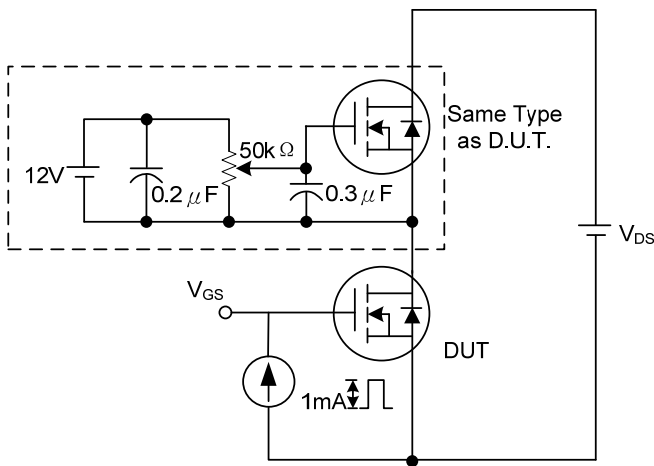
TEST CIRCUITS AND WAVEFORMS (Cont.)



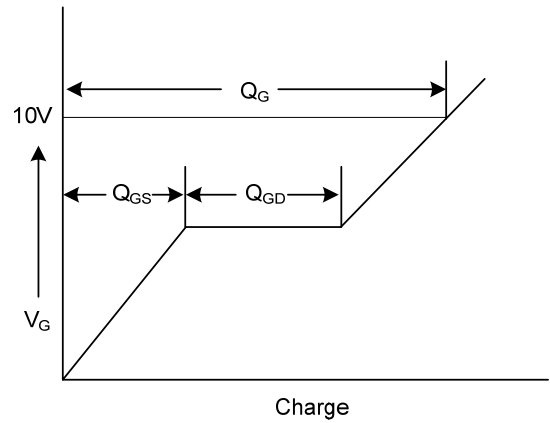
Switching Test Circuit



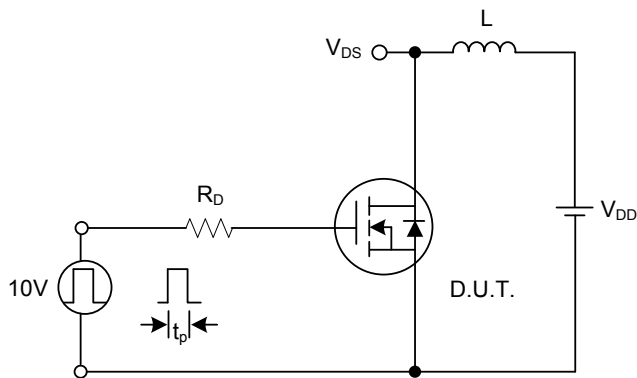
Switching Waveforms



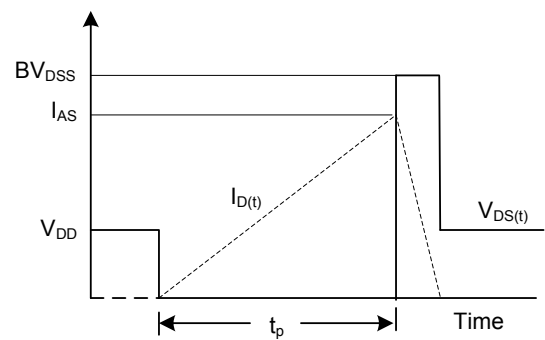
Gate Charge Test Circuit



Gate Charge Waveform

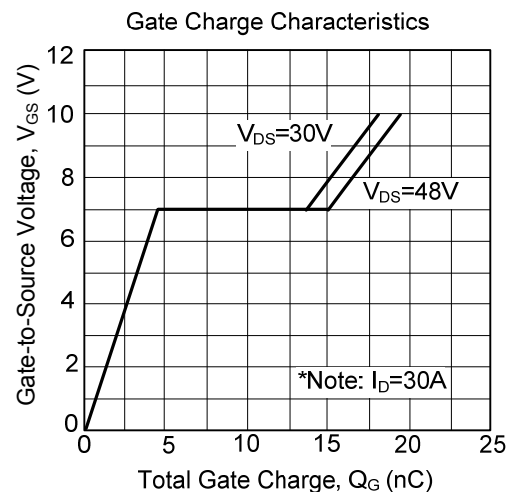
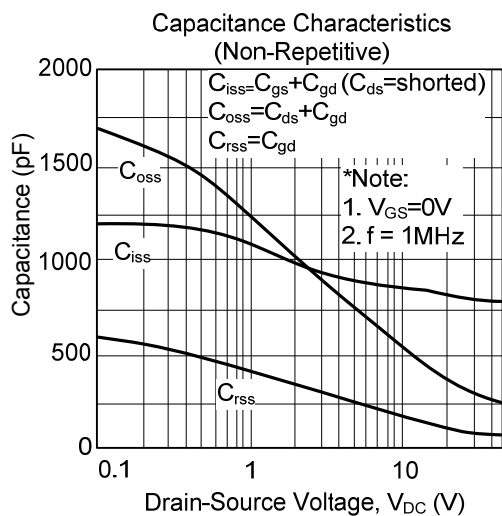
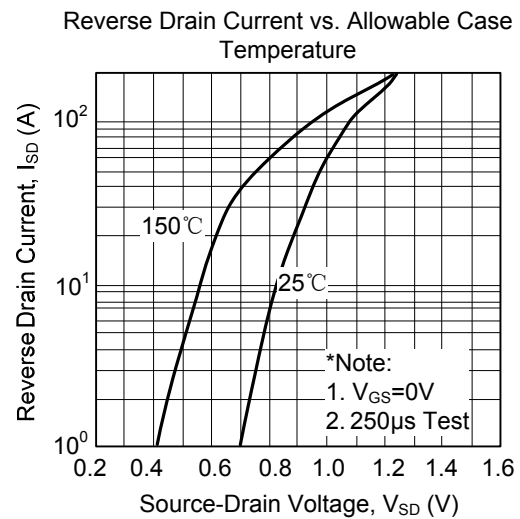
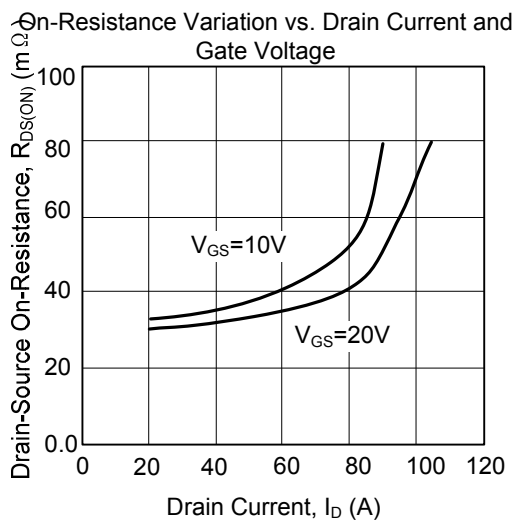
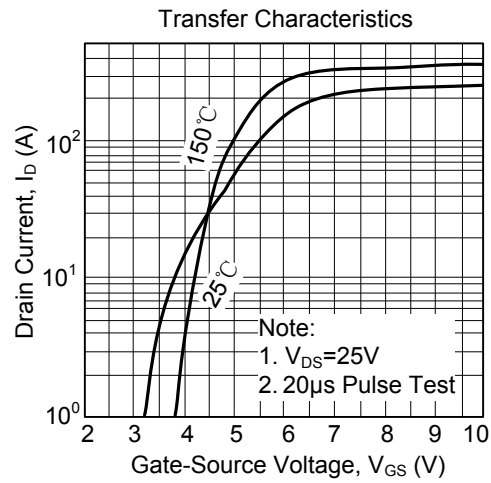
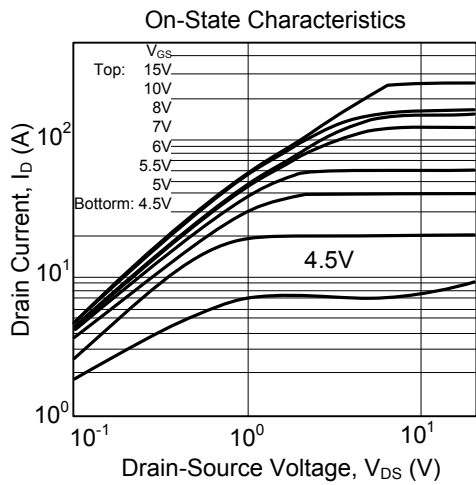


Unclamped Inductive Switching Test Circuit

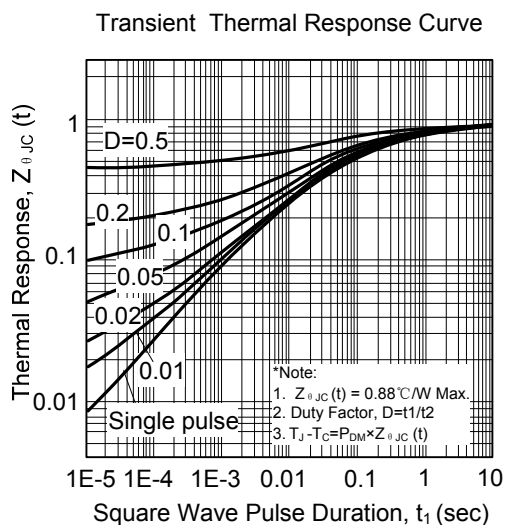
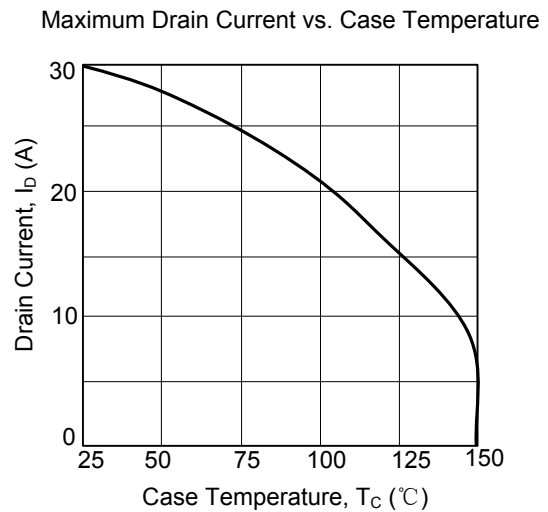
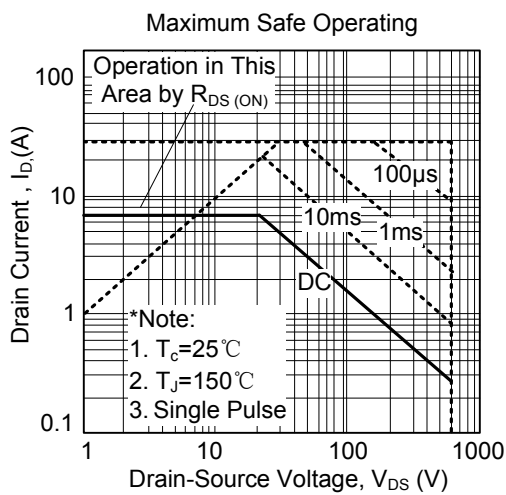
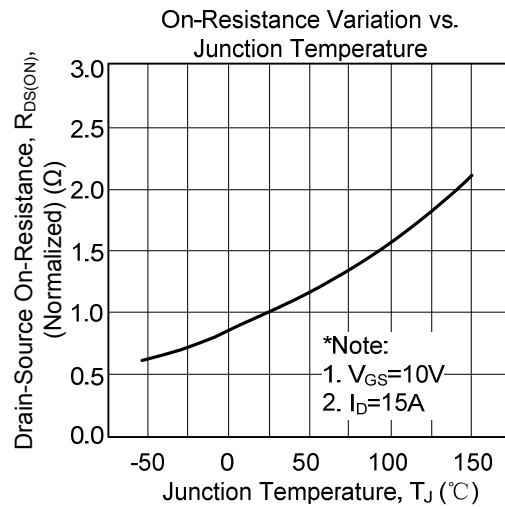
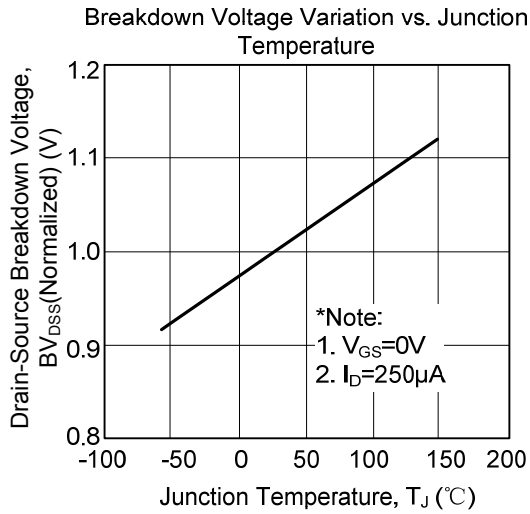


Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



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